

2N4410



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 50 mA. Sourced from Process 16. See 2N5551 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V_{CEO}	Collector-Emitter Voltage	80	V	
V _{CBO}	Collector-Base Voltage	120	V	
V_{EBO}	Emitter-Base Voltage	5.0	V	
I _C	Collector Current - Continuous	200	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted			
Symbol	Characteristic	Мах	Units
		2N4410	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
R _{θJC}	Thermal Resistance, Junction to Ambient	200	°C/W

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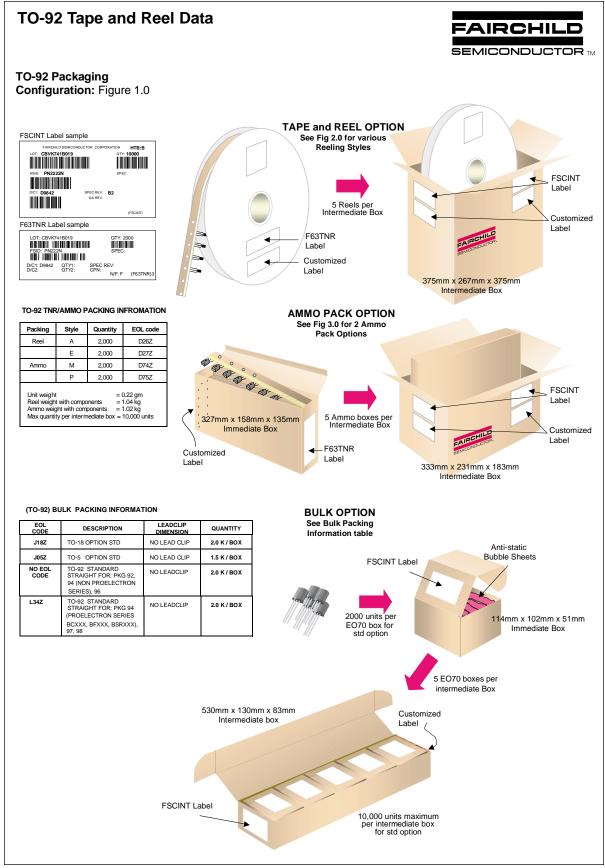
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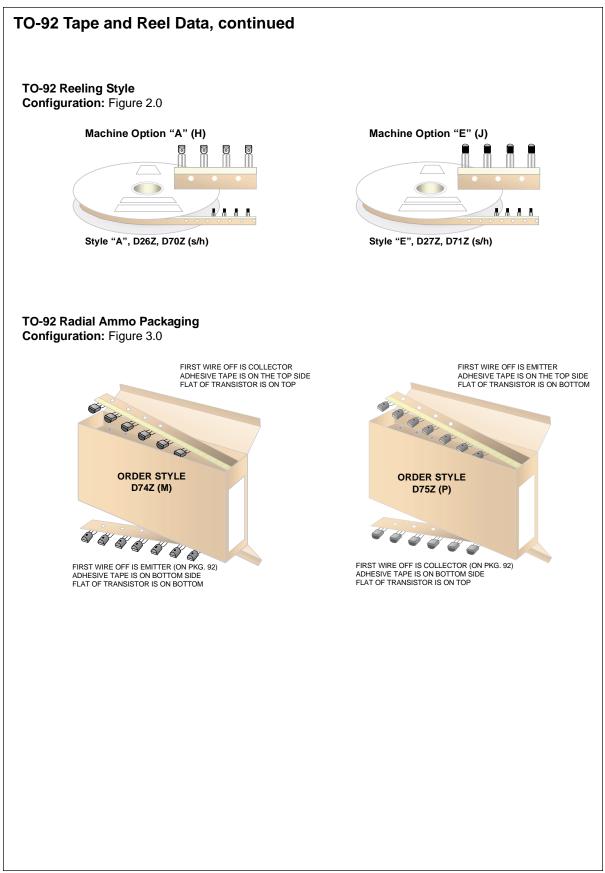
Electr	Electrical Characteristics TA = 25°C unless otherwise noted				
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	80		V
$V_{(BR)CEX}$	Collector-Emitter Breakdown Voltage	$I_{C} = 500 \ \mu A, V_{BB} = 5.0 \ V$ $R_{BE} = 8.2 \ k\Omega$	120		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu {\rm A}, \ I_{\rm E} = 0$	120		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \ \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_E = 0$ $V_{CB} = 100 \text{ V}, I_F = 0, T_A = 100 ^{\circ}\text{C}$	10 1.0		nA μA
I _{EBO}	Emitter Cutoff Current	$V_{CB} = 100 \text{ V}, I_E = 0, T_A = 100 ^{\circ}\text{C}$ $V_{EB} = 4.0 \text{ V}, I_C = 0$	100		nA
ON CHAR	ACTERISTICS* DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_{C} = 10 \text{ mA}$	60 60	400	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ W}, I_C = 10 \text{ MA}$ $I_C = 1.0 \text{ mA}, I_B = 0.1 \text{ mA}$	00	0.2	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 1.0 {\rm mA}, I_{\rm B} = 0.1 {\rm mA}$		0.8	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ mA}$		0.8	V
SMALL S	IGNAL CHARACTERISTICS				
C _{ob}	Output Capacitance	V _{CB} = 10 V, f = 100 kHz		12	pF
C _{ib}	Input Capacitance	V _{EB} = 0.5 V, f = 100 kHz		50	pF
h _{fe}	Small-Signal Current Gain	$I_{c} = 10 \text{ mA}, V_{ce} = 10 \text{ V},$ f = 30 MHz	2.0	10	

*Pulse Test: Pulse Width $\leq 300~\mu s,~\text{Duty}~\text{Cycle} \leq 2.0\%$

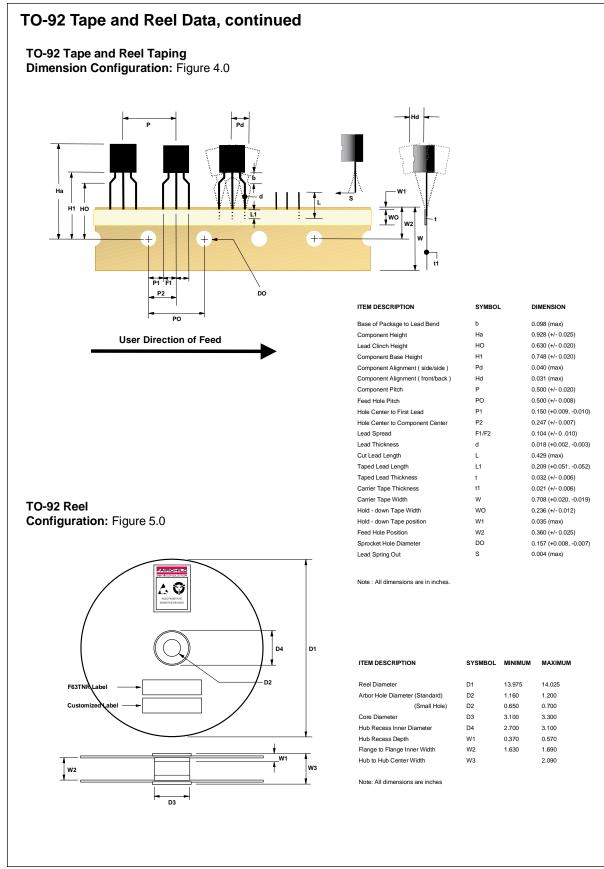


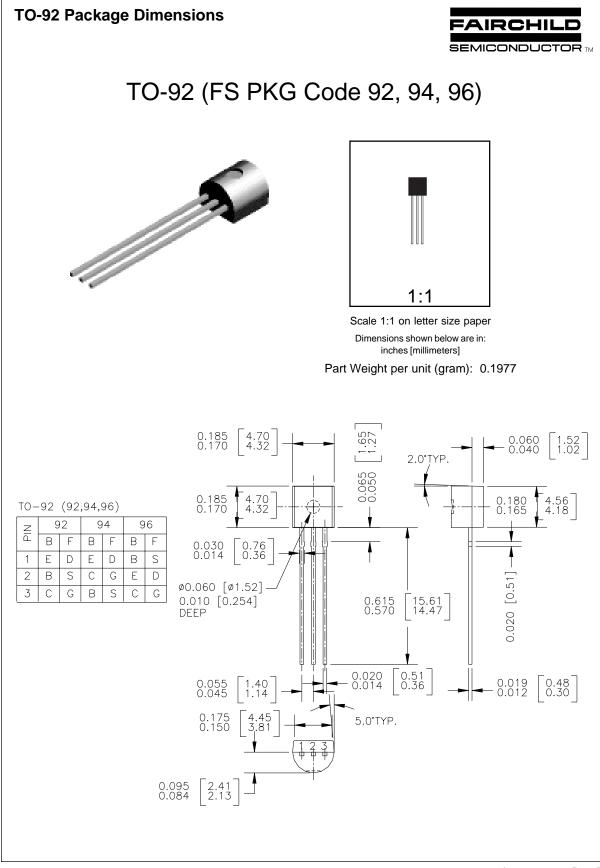
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